

- L6: (177332) insula\$4 dielectric
- L7: (366759) spacer
- L8: (2030220)L6 L7
- L9: (38431) rie
- L10: (5000) fluorin\$4 near2 etch\$4
- L11: (6877) fluorin\$4 near3 etch\$4
- L12: (8114) fluorin\$4 near4 etch\$4
- L13: (8748) ion adj. milling
- L14: (900) 9 with 13
- L15: (32) 14 same 12
- L16: (1157) 9 same 13
- L17: (36) 16 same 12
- L18: (50314) 8 near3 5
- L19: (11) 15 and 18
- L20: (42674) 12 9
- L21: (1218) 20 same 13
- L22: (13) 21 same 18
- L23: (43359) 13 9
- L24: (766) 23 same 12
- L25: (18) 24 same 18
- L26: (33221) etch\$4 adj. rate
- L27: (4163689) control \$4
- L28: (436) 26 with 18
- L29: (13) 20 with 27
- L30: (68) 18 with 4

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ORs: US PGPUB USPAT EPO JPO GERVENT IBM TDB

Default operator: OR [ ]

28 with 27.

*Jan. 2005*

    

#	Invator	Document#	Issue P	Title	Current	CurrentX	Retrieval	SEC	P	Image	Doc	P
1	<input type="checkbox"/>	Park, Il-Yong	US 2004021	Method of manufacturing MOS transistor having short channel and long gate length	438/197	438/589		P	C	C	C	US 2004021
2	<input checked="" type="checkbox"/>	Park, Il-Yong	US 2004009	Method of manufacturing MOS transistor having short channel and long gate length	257/327	257/328		P	F	F	F	US 2004009
3	<input checked="" type="checkbox"/>	Tanigami, Ta	US 2002017	Process for manufacturing semiconductor device	438/263	257/E21.68		P	F	F	C	US 2002017
4	<input checked="" type="checkbox"/>	Lin, Bih-Tao	US 2002013	Fabrication method of shallow trench isolation	438/424	257/E21.54		P	C	C	C	US 2002013
5	<input checked="" type="checkbox"/>	Tanigami, Ta	US 6589844	Process for manufacturing semiconductor device	438/281	257/E21.68		P	F	F	F	US 6589844
6	<input checked="" type="checkbox"/>	Tanigami, Ta	US 6441430	200204 Semiconductor device with floating gates	257/317	257/315		P	F	F	C	US 6441430
7	<input checked="" type="checkbox"/>	Sakao, Masa	US 6228170	200101 Semiconductor memory cell	257/286	257/306		P	C	C	C	US 6228170
8	<input checked="" type="checkbox"/>	Masuda, Sa	US 5994743	199911 Semiconductor device having different side	257/889	257/900		P	C	C	C	US 5994743
9	<input checked="" type="checkbox"/>	Wu, Der-Yuan et al	US 5854108	199811 Method of forming a data storage capacitor	438/253	257/E21.64		P	F	F	C	US 5854108
10	<input checked="" type="checkbox"/>	Sun, Yi-Lin et al	US 5834346	199811 Procedure for eliminating bubbles formed during fabrication	438/231	257/E21.24		P	F	F	C	US 5834346

  

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